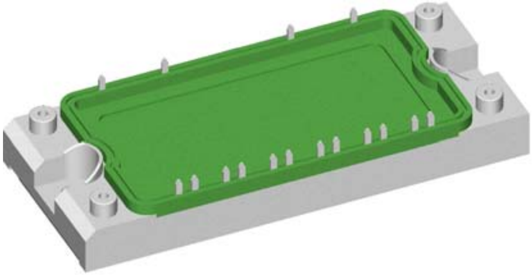
Standard Rectifier Module

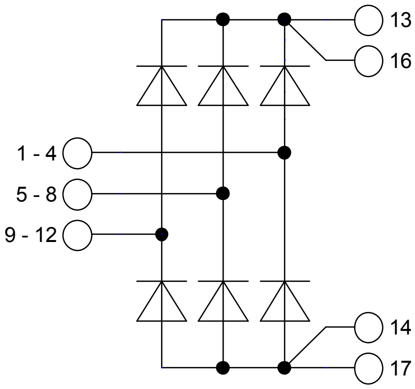
3~ Rectifier		
V_{RRM}	=	1600 V
I_{DAV}	=	120 A
I_{FSM}	=	700 A

3~ Rectifier Bridge

Part number

VUO121-16NO1





E72873

Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling

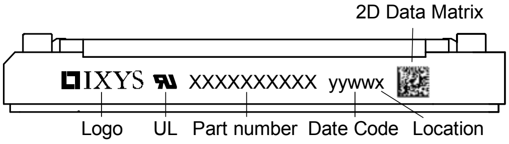
Data according to IEC 60747and per semiconductor unless otherwise specified

Rectifier

Symbol	Definition	Conditions		Ratings			
				min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			100	µA
		V_R = 1600 V	T_{VJ} = 150°C			1.5	mA
V_F	*forward voltage drop*	I_F = 40 A	T_{VJ} = 25°C			1.19	V
		I_F = 120 A				1.64	V
		I_F = 40 A	T_{VJ} = 125°C			1.12	V
		I_F = 120 A				1.70	V
I_{DAV}	*bridge output current*	T_C = 105°C	T_{VJ} = 150°C			120	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.80	V
r_F	*slope resistance*					7.6	mΩ
R_{thJC}	*thermal resistance junction to case*					0.65	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			190	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			700	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			755	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			595	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			645	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			2.45	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.37	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			1.77	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.73	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		27		pF

Package E2-Pack

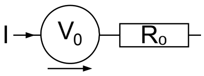
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal				200	A
T_{stg}	*storage temperature*			-40		125	°C
T_{VJ}	*virtual junction temperature*			-40		150	°C
Weight					176		g
M_D	*mounting torque*			3		6	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	6.0			mm
$d_{Spb/Apb}$			*terminal to backside*	12.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO121-16NO1	VUO121-16NO1	Box	6	496278

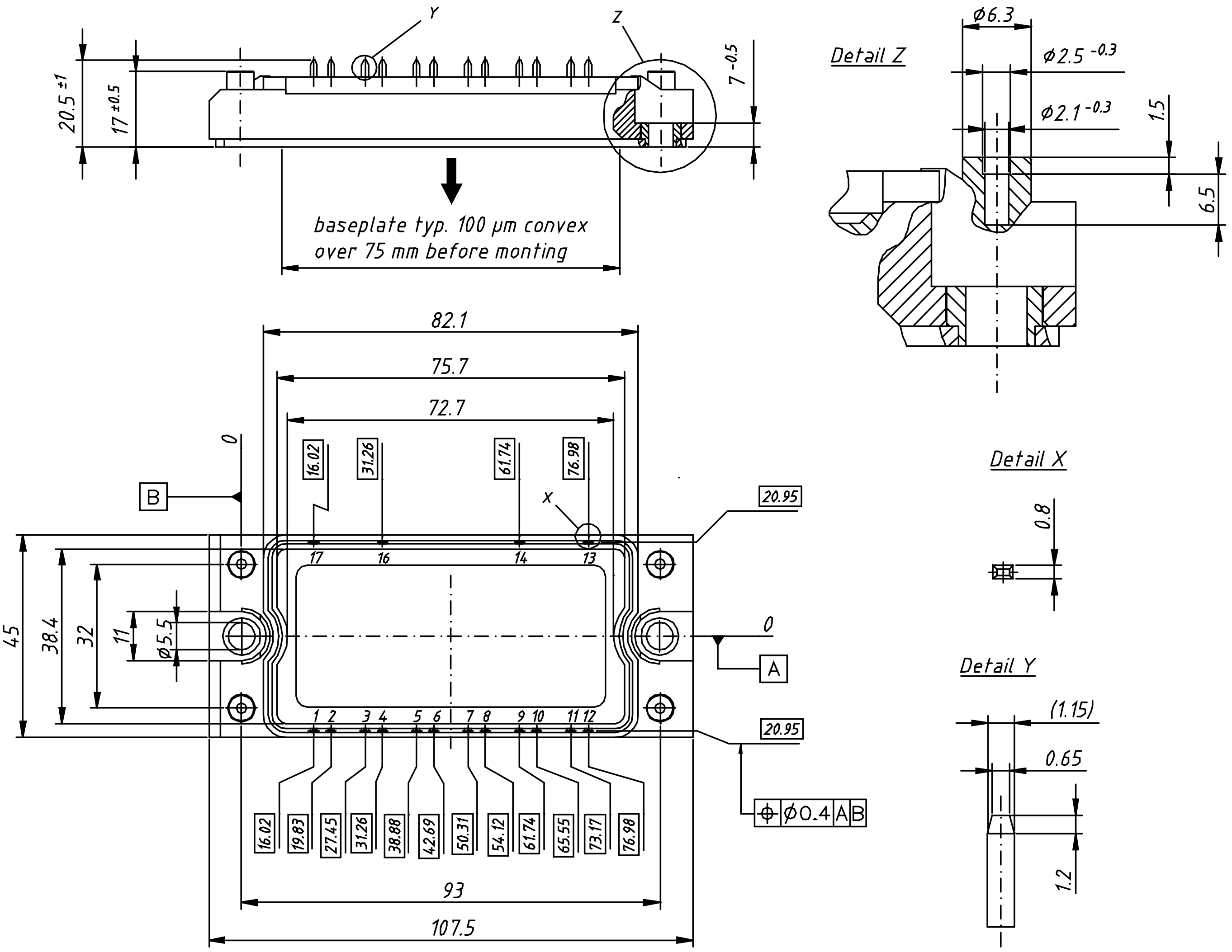
Equivalent Circuits for Simulation

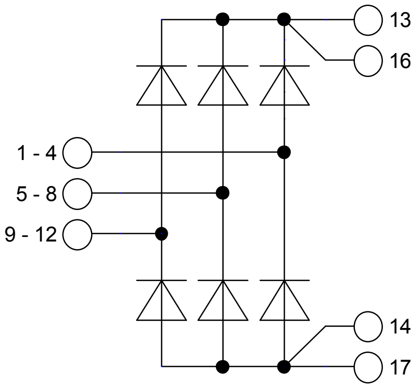
* on die level $T_{VJ} = 150\,°C$



		Rectifier	
$V_{0\,max}$	*threshold voltage*	0.8	V
$R_{0\,max}$	*slope resistance **	4.5	mΩ

Outlines E2-Pack





Rectifier

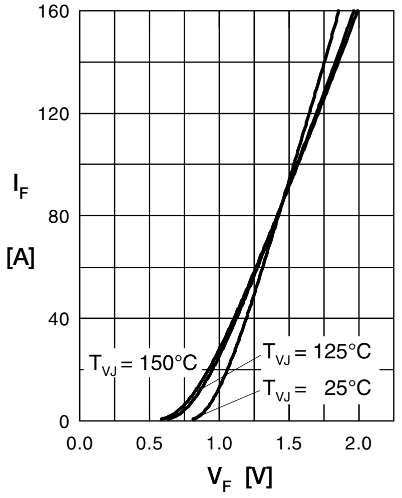


Fig. 1 Forward current vs. voltage drop per diode

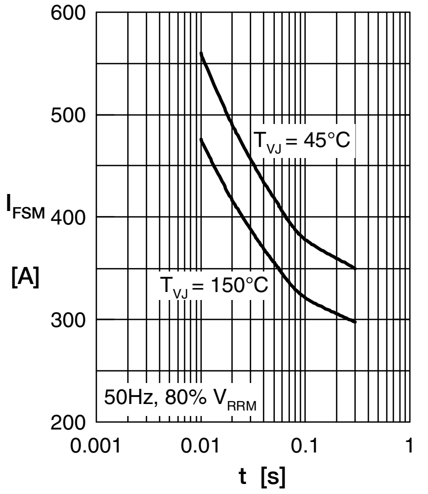


Fig. 2 Surge overload current vs. time per diode

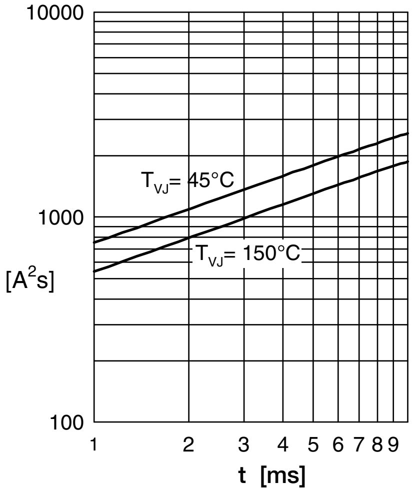


Fig. 3 I^2t vs. time per diode

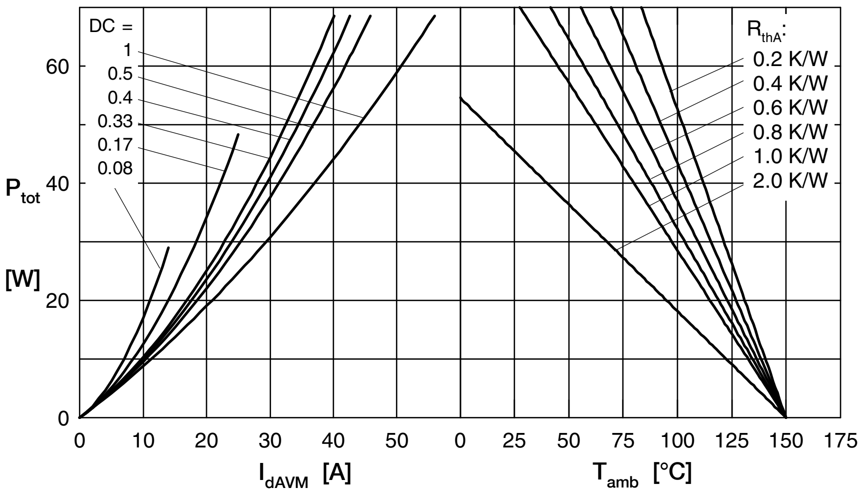


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

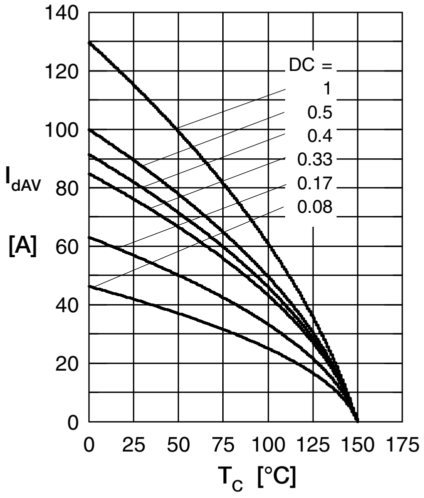


Fig. 5 Max. forward current vs. case temperature per diode

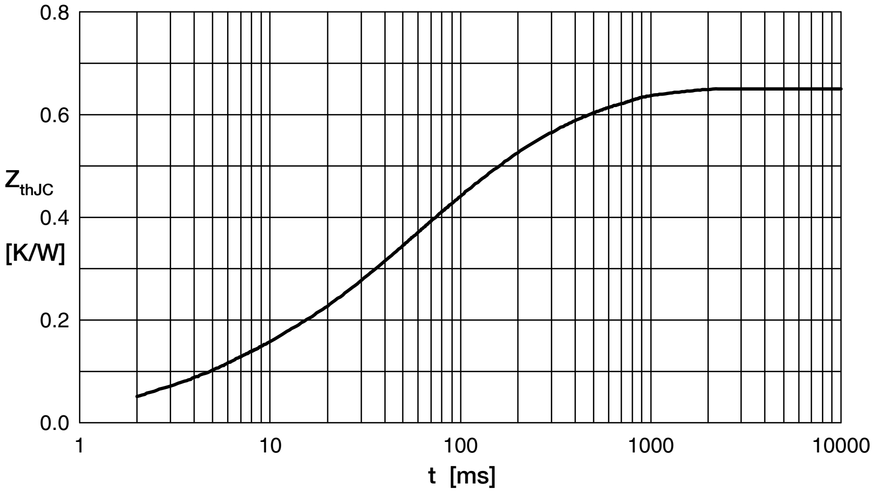


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.080	0.004
0.003	0.010
0.160	0.025
0.160	0.400
0.247	0.090

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